

2SD1277, 2SD1277A

Silicon NPN triple diffusion planar type Darlington

For midium speed power switching

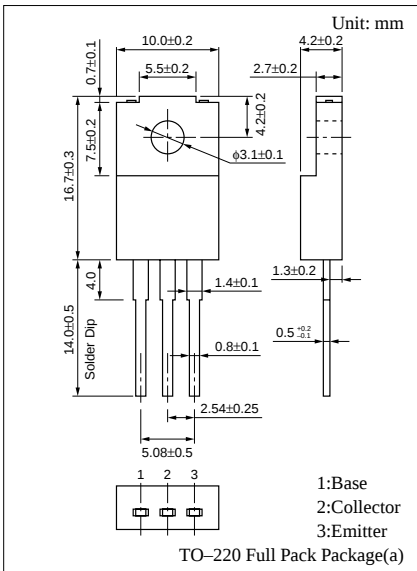
Complementary to 2SB951 and 2SB951A

■ Features

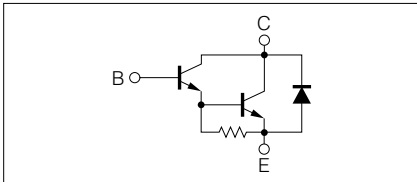
- High foward current transfer ratio h_{FE}
- High-speed switching
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	60	V
Collector to emitter voltage	V_{CEO}	80	V
Emitter to base voltage	V_{EBO}	7	V
Peak collector current	I_{CP}	12	A
Collector current	I_C	8	A
Collector power dissipation	P_C	45	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Internal Connection

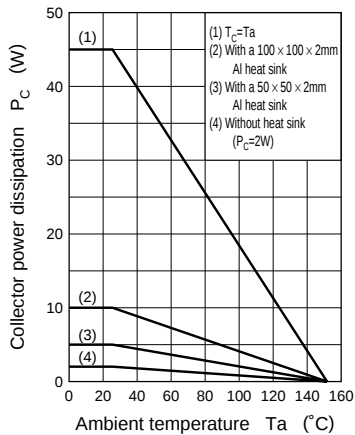
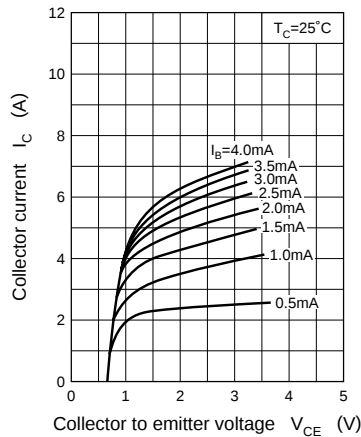
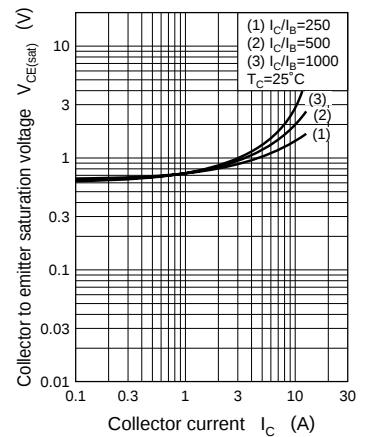
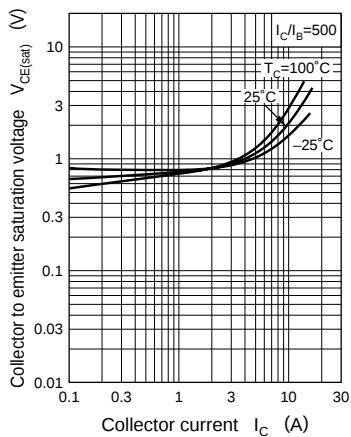
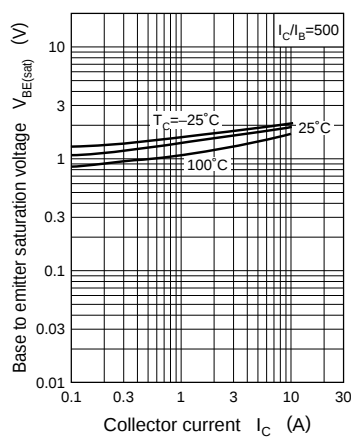
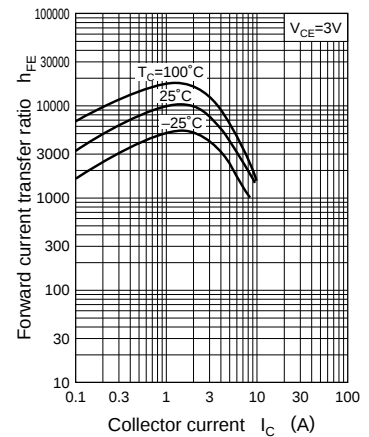


■ Electrical Characteristics ($T_C=25^\circ\text{C}$)

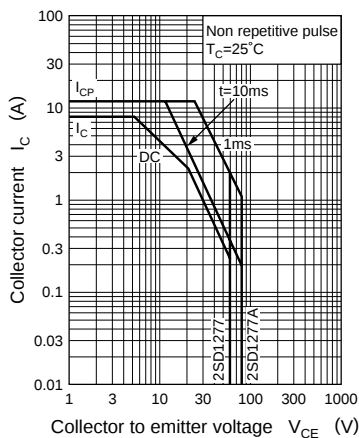
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 60V, I_E = 0$			100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 7V, I_C = 0$			2	mA
Collector to emitter voltage	V_{CEO}	$I_C = 30\text{mA}, I_B = 0$	60			V
Forward current transfer ratio	h_{FE1}^*	$V_{CE} = 3V, I_C = 4A$	2000		10000	
	h_{FE2}	$V_{CE} = 3V, I_C = 8A$	500			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 4A, I_B = 8\text{mA}$			1.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 4A, I_B = 8\text{mA}$			2	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 0.5A, f = 1\text{MHz}$	20			MHz
Turn-on time	t_{on}	$I_C = 4A, I_{B1} = 8\text{mA}, I_{B2} = -8\text{mA}, V_{CC} = 50V$		0.5		μs
Storage time	t_{stg}			4		μs
Fall time	t_f			1		μs

* h_{FE1} Rank classification

Rank	Q	P
h_{FE1}	2000 to 5000	4000 to 10000

$P_C - T_a$  $I_C - V_{CE}$  $V_{CE(sat)} - I_C$  $V_{CE(sat)} - I_C$  $V_{CB(sat)} - I_C$  $h_{FE} - I_C$ 

Area of safe operation (ASO)

 $R_{th(t)} - t$ 